CSD17308Q3 30-V N-Channel NexFET™ Power MOSFETs

1 Features

- Optimized for 5-V gate drive
- Ultra-low Q_g and Q_{gd}
- Low thermal resistance
- Avalanche rated
- Lead-free terminal plating
- RoHS compliant
- Halogen free
- VSON 3.3 mm × 3.3 mm plastic package

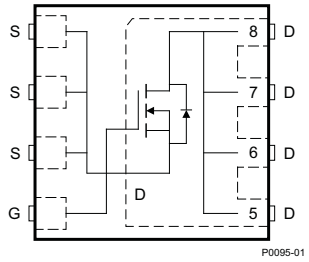
2 Applications

- Notebook point of load
- Point-of-load synchronous buck in networking, telecom, and computing systems

3 Description

This 30-V, 8.2-mΩ, 3.3 mm × 3.3 mm VSON NexFET™ power MOSFET is designed to minimize losses in power conversion applications and optimized for 5-V gate drive applications.

Top View



Product Summary

T_A = 25°C		VALUE		UNIT
V_{DS}	Drain-to-source voltage	30		V
Q_g	Gate charge total (4.5 V)	3.9		nC
Q_{gd}	Gate charge gate-to-drain	0.8		nC
$R_{DS(on)}$	Drain-to-source on-resistance	V_{GS} = 3 V	12.5	mΩ
		V_{GS} = 4.5 V	9.4	
		V_{GS} = 8 V	8.2	
$V_{GS(th)}$	Threshold voltage	1.3		V

Device Information(1)

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD17308Q3	2500	13-Inch Reel	SON 3.30 mm × 3.30 mm Plastic Package	Tape and Reel

(1) For all available packages, see the orderable addendum at the end of the data sheet.

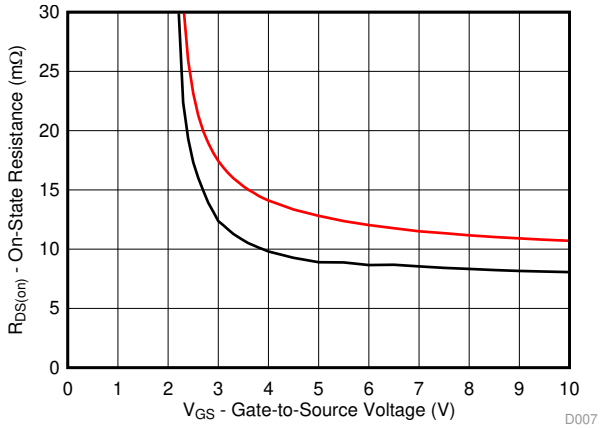
Absolute Maximum Ratings

T_A = 25°C unless otherwise stated		VALUE	UNIT
V_{DS}	Drain-to-source voltage	30	V
V_{GS}	Gate-to-source voltage	+10 / –8	V
I_D	Continuous drain current (package limited)	50	A
	Continuous drain current, T_C = 25°C	44	
	Continuous drain current(1)	14	
I_{DM}	Pulsed drain current, T_A = 25°C(2)	167	A
P_D	Power dissipation(1)	2.7	W
	Power dissipation, T_C = 25°C	28	
T_J, T_{stg}	Operating junction and storage temperature	–55 to 150	°C
E_{AS}	Avalanche energy, single pulse I_D = 36 A, L = 0.1 mH, R_G = 25 Ω	65	mJ

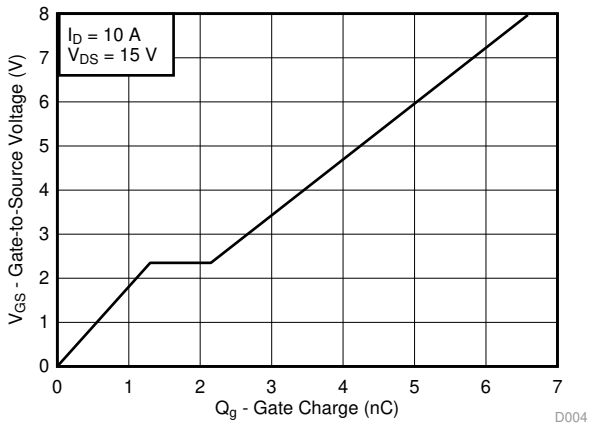
(1) Typical $R_{\theta JA}$ = 46°C/W when mounted on a 1-in^2 (6.45-cm^2), 2-oz (0.071-mm) thick Cu pad on a 0.06-in (1.52-mm) thick FR4 PCB.

(2) Max $R_{\theta JC}$ = 4.5°C/W, pulse duration ≤ 100 µs, duty cycle ≤ 1%.

$R_{DS(on)}$ vs V_{GS}



Gate Charge



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (October 2015) to Revision C — **Page**

- Changed $V_{GS(th)}$ MAX specification in the *Electrical Characteristics* table, From 1.8 V : To 1.6 V ... 3

Changes from Revision A (February 2010) to Revision B — **Page**

- Added part number to title ... 1
- Added Package Limited Continuous Drain Current ... 1
- Added line for Power Dissipation, T_C = 25°C in *Absolute Maximum Ratings* table ... 1
- Updated pulsed current conditions ... 1
- Updated Figure 1 to show $R_{\theta JC}$ curves ... 5
- Added 4.5 V curve in Figure 8 ... 6
- Updated Figure 10 ... 7
- Added the *Device and Documentation Support* section ... 8
- Updated the Mechanical, Packaging, and Orderable Information section ... 9

Changes from Original (February 2010) to Revision A — **Page**

- Deleted the Package Marking Information section ... 11

5 Specifications

5.1 Electrical Characteristics

T_A = 25°C unless otherwise stated

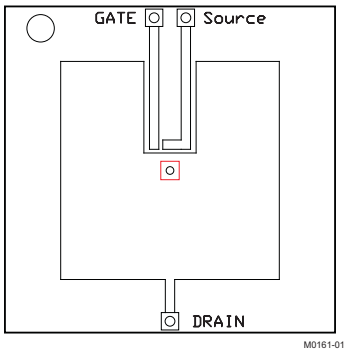
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-source voltage	V_{GS} = 0 V, I_D = 250 μA	30			V
I_{DSS}	Drain-to-source leakage current	V_{GS} = 0 V, V_{DS} = 24 V			1	μA
I_{GSS}	Gate-to-source leakage current	V_{DS} = 0 V, V_{GS} = +10 / –8 V			100	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	V_{DS} = V_{GS}, I_D = 250 μA	0.9	1.3	1.6	V
$R_{DS(on)}$	Drain-to-source on-resistance	V_{GS} = 3 V, I_D = 10 A		12.5	16.5	mΩ
		V_{GS} = 4.5 V, I_D = 10 A		9.4	11.8	
		V_{GS} = 8 V, I_D = 10 A		8.2	10.3	
g_{fs}	Transconductance	V_{DS} = 15 V, I_D = 10 A		37		S
DYNAMIC CHARACTERISTICS						
C_{ISS}	Input capacitance	V_{GS} = 0 V, V_{DS} = 15 V, f = 1 MHz		540	700	pF
C_{OSS}	Output capacitance			280	365	pF
C_{RSS}	Reverse transfer capacitance			27	35	pF
R_g	Series gate resistance			0.9	1.8	Ω
Q_g	Gate charge total (4.5 V)	V_{DS} = 15 V, I_D = 10 A		3.9	5.1	nC
Q_{gd}	Gate charge gate-to-drain			0.8		nC
Q_{gs}	Gate charge gate-to-source			1.3		nC
$Q_{g(th)}$	Gate charge at V_{th}			0.7		nC
Q_{OSS}	Output charge	V_{DS} = 13 V, V_{GS} = 0 V		7.4		nC
$t_{d(on)}$	Turnon delay time	V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 10 A, R_G = 2 Ω		4.5		ns
t_r	Rise time			5.7		ns
$t_{d(off)}$	Turnoff delay time			9.9		ns
t_f	Fall time			2.3		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode forward voltage	I_{DS} = 10 A, V_{GS} = 0 V		0.85	1	V
Q_{rr}	Reverse recovery charge	V_{DD} = 13 V, I_F = 10 A, di/dt = 300 A/μs		9.3		nC
t_{rr}	Reverse recovery time			14.3		ns

5.2 Thermal Information

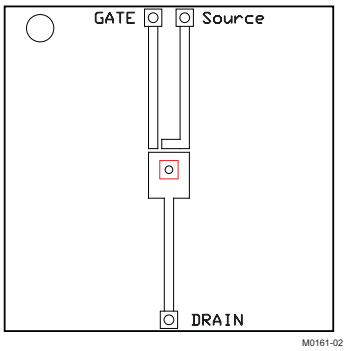
T_A = 25°C unless otherwise stated

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance (1)			4.5	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance (1) (2)			58	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-in^2 (6.45-cm^2), 2-oz (0.071-mm) thick Cu pad on a 1.5-in × 1.5-in (3.81-cm × 3.81-cm), 0.06-in (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1-in^2 (6.45-cm^2), 2-oz (0.071-mm) thick Cu.



Max $R_{\theta JA}$ = 58°C/W when mounted on 1 in^2 (6.45 cm^2) of 2-oz (0.071-mm) thick Cu.



Max $R_{\theta JA}$ = 165°C/W when mounted on a minimum pad area of 2-oz (0.071-mm) thick) Cu.

5.3 Typical MOSFET Characteristics

T_A = 25°C unless otherwise stated

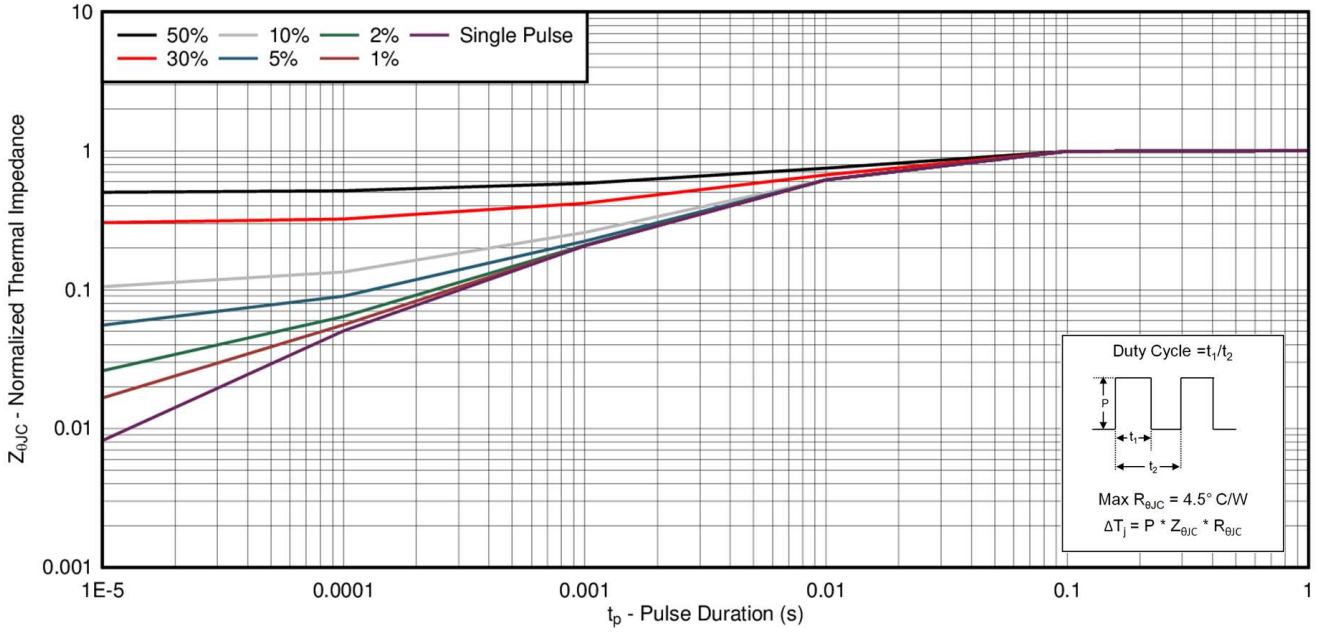


Figure 1. Transient Thermal Impedance

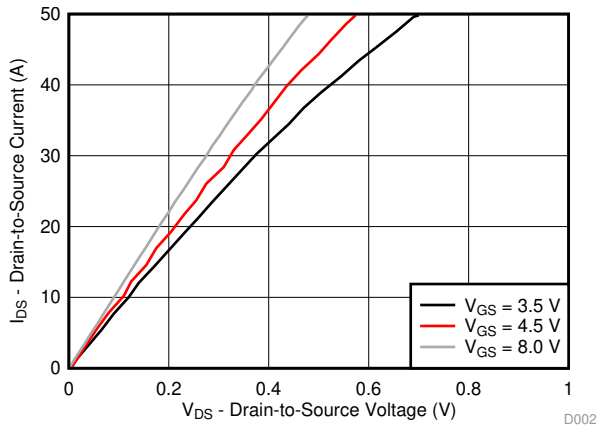


Figure 2. Saturation Characteristics

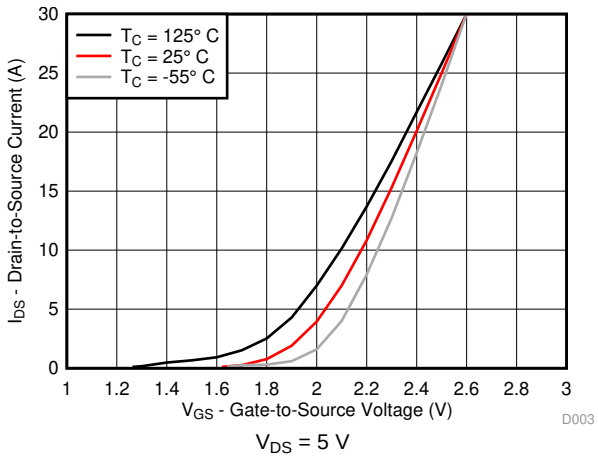


Figure 3. Transfer Characteristics

Typical MOSFET Characteristics (continued)

T_A = 25°C unless otherwise stated

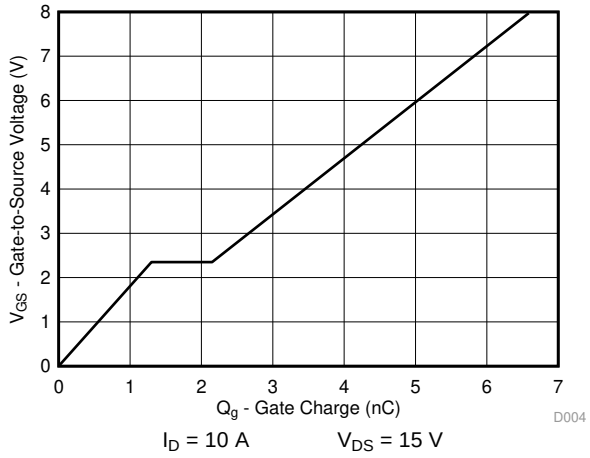


Figure 4. Gate Charge

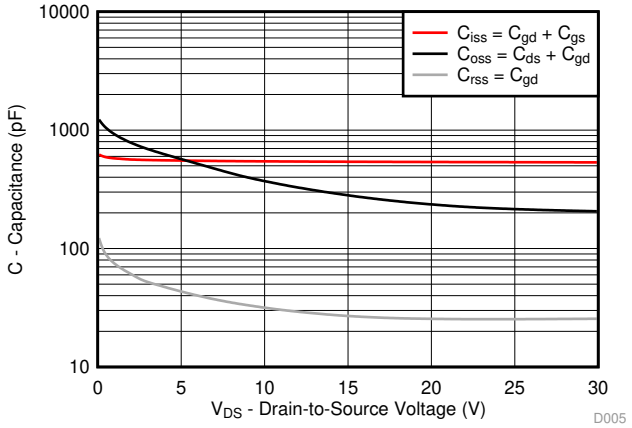


Figure 5. Capacitance

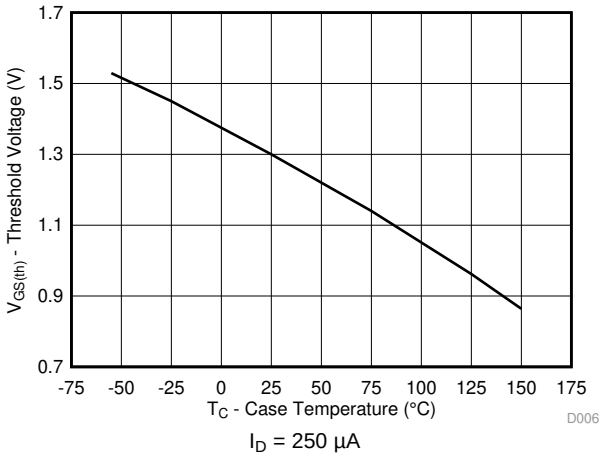


Figure 6. Threshold Voltage vs Temperature

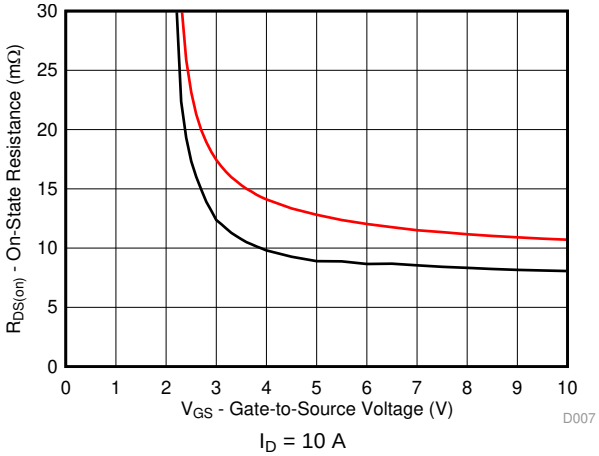


Figure 7. On-State Resistance vs Gate-to-Source Voltage

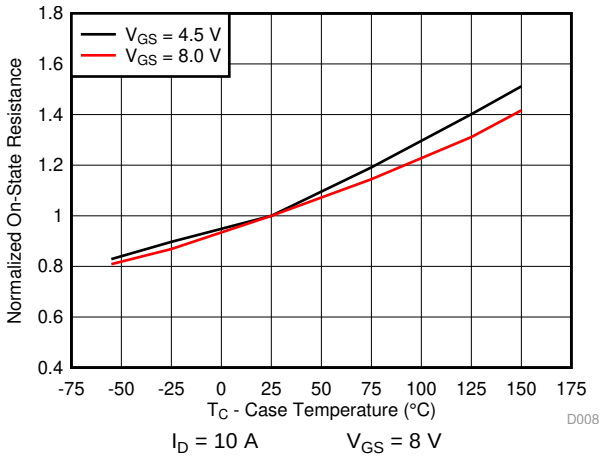


Figure 8. Normalized On-State Resistance vs Temperature

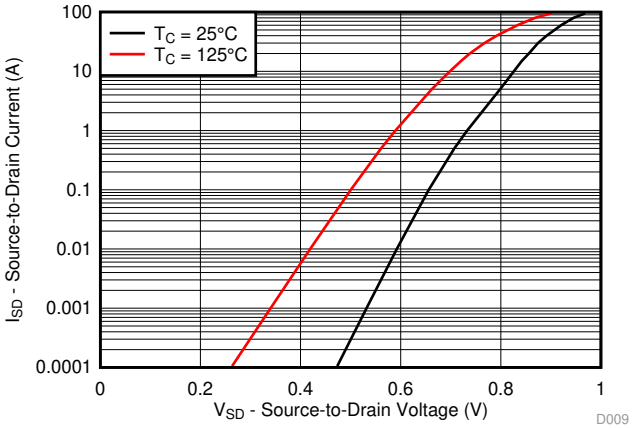
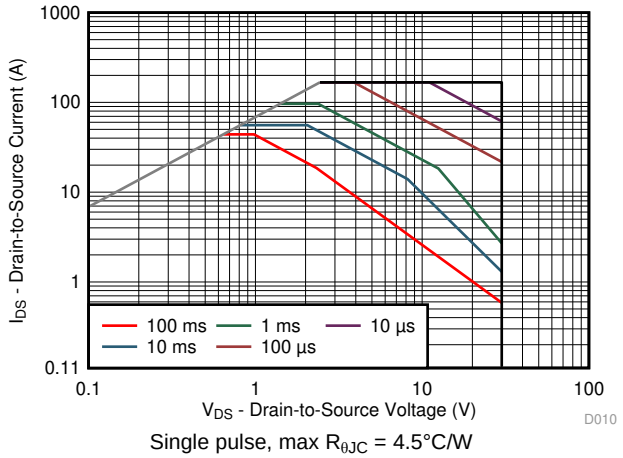


Figure 9. Typical Diode Forward Voltage

Typical MOSFET Characteristics (continued)

T_A = 25°C unless otherwise stated



Single pulse, max $R_{\theta JC}$ = 4.5°C/W

Figure 10. Maximum Safe Operating Area

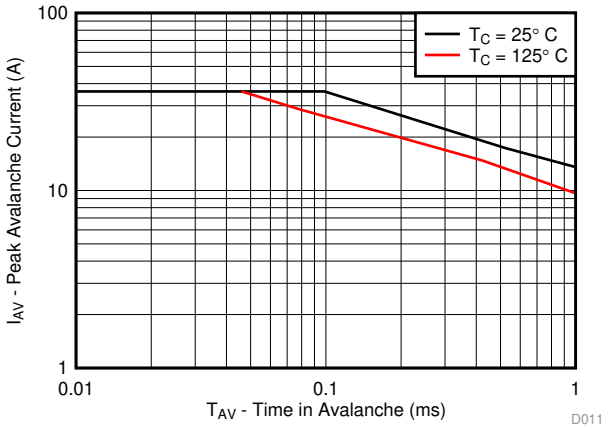


Figure 11. Single Pulse Unclamped Inductive Switching

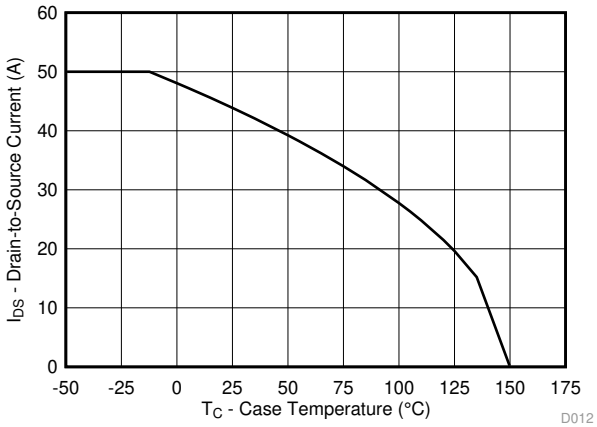


Figure 12. Maximum Drain Current vs Temperature

6 Device and Documentation Support

6.1 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

6.2 Trademarks

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All other trademarks are the property of their respective owners.

6.3 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.4 Glossary

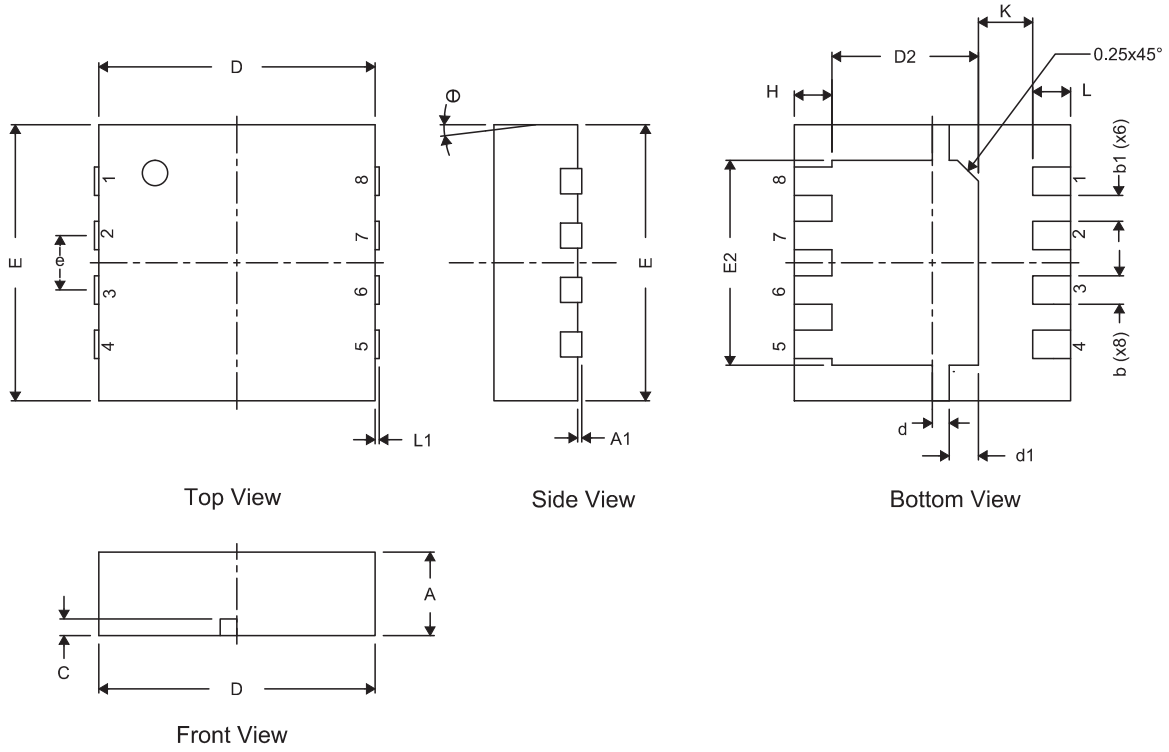
SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 Mechanical, Packaging, and Orderable Information

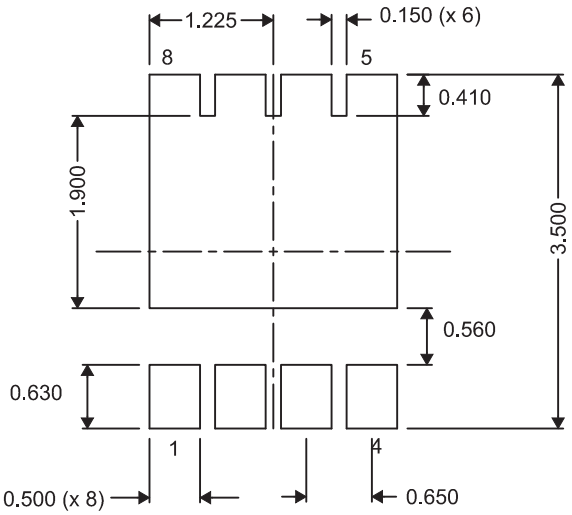
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Q3 Package Dimensions



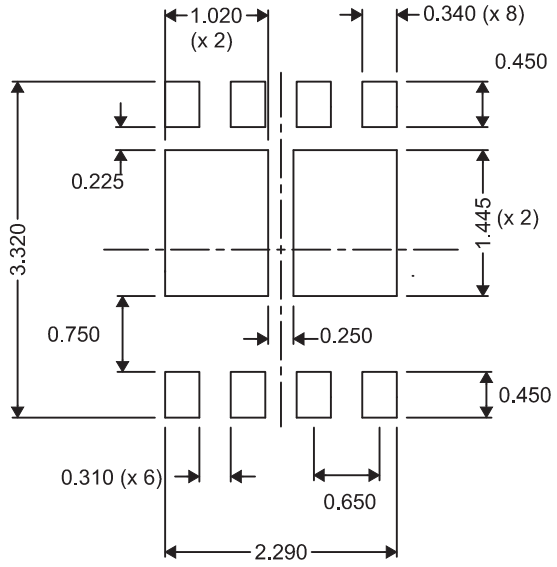
DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.950	1.000	1.100	0.037	0.039	0.043
A1	0.000	0.000	0.050	0.000	0.000	0.002
b	0.280	0.340	0.400	0.011	0.013	0.016
b1		0.310 NOM			0.012 NOM	
c	0.150	0.200	0.250	0.006	0.008	0.010
D	3.200	3.300	3.400	0.126	0.130	0.134
D2	1.650	1.750	1.800	0.065	0.069	0.071
d	0.150	0.200	0.250	0.006	0.008	0.010
d1	0.300	0.350	0.400	0.012	0.014	0.016
E	3.200	3.300	3.400	0.126	0.130	0.134
E2	2.350	2.450	2.550	0.093	0.096	0.100
e		0.650 TYP			0.026 TYP	
H	0.35	0.450	0.550	0.014	0.018	0.022
K		0.650 TYP			0.026 TYP	
L	0.35	0.450	0.550	0.014	0.018	0.022
L1	0	—	0	0	—	0
θ	0	—	0	0	—	0

7.2 Recommended PCB Pattern



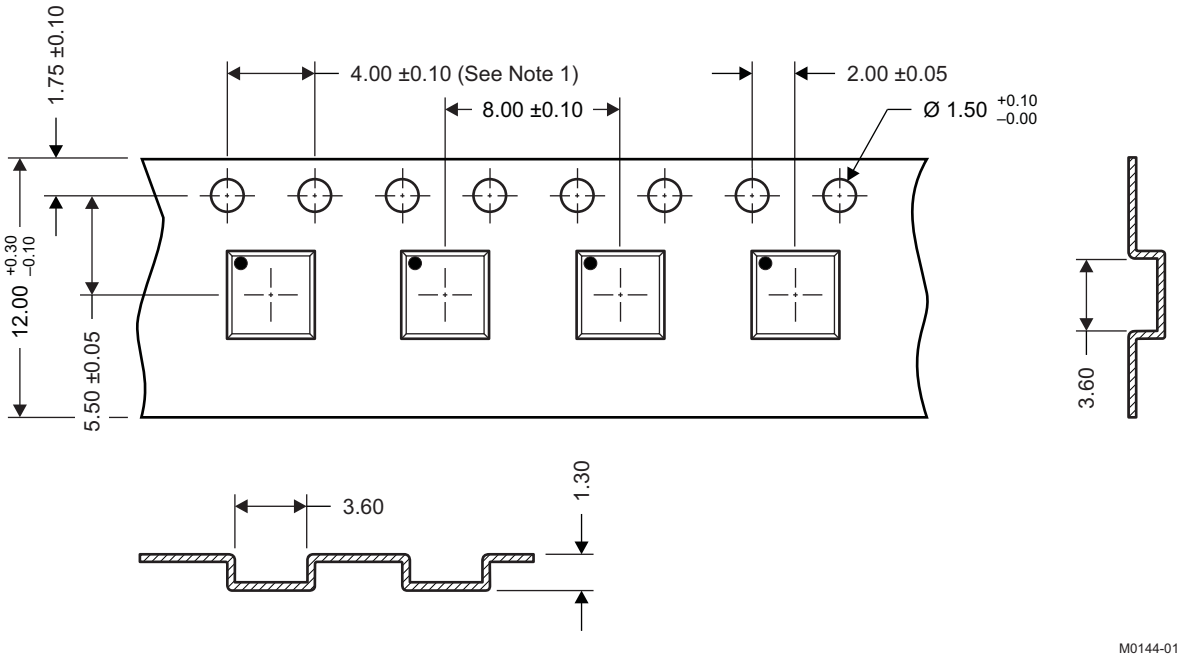
For recommended circuit layout for PCB designs, see application note SLPA005 – *Reducing Ringing Through PCB Layout Techniques*.

7.3 Recommended Stencil Opening



All dimensions are in mm, unless otherwise specified.

7.4 Q3 Tape and Reel Information



Notes:

1. 10 sprocket hole pitch cumulative tolerance ±0.2
2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
3. Material: black static dissipative polystyrene
4. All dimensions are in mm (unless otherwise specified).
5. Thickness: 0.30 ±0.05 mm
6. MSL1 260°C (IR and Convection) PbF-Reflow Compatible

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD17308Q3	ACTIVE	VSON-CLIP	DQG	8	2500	RoHS-Exempt & Green	SN	Level-1-260C-UNLIM	-55 to 150	CSD17308	Samples
CSD17308Q3T	ACTIVE	VSON-CLIP	DQG	8	250	RoHS-Exempt & Green	SN	Level-1-260C-UNLIM	-55 to 150	CSD17308	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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